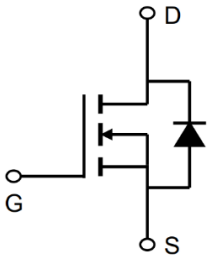
AP150N04D

40V N-Channel Enhancement Mode MOSFET

Description

The AP150N04D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

V_{DS} = 40V I_D =150 A

$R_{DS(ON)}$ < 2.4mΩ @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP150N04D	TO-252-3L	AP150N04D XXX YYYY	2500

Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	40	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	150	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	90	A
IDM	Pulsed Drain Current[2]	450	A
EAS	Single Pulse Avalanche Energy[3]	400	mJ
IAS	Avalanche Current	40	A
P_D@T_C=25℃	Total Power Dissipation[4]	125	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
RθJA	Thermal Resistance Junction-Ambient [1]	50	℃/W
RθJC	Thermal Resistance Junction-Case[1]	1	℃/W

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Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	2.0	2.3	
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V , I_D=20A	---	2.7	3.0	mΩ
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.6	2.2	V
IDSS	Drain-Source Leakage Current	V_{DS}=32V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=32V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	53	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.0	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=10V , I_D=20A	---	45	---	nC
Qgs	Gate-Source Charge		---	12	---	
Qgd	Gate-Drain Charge		---	18.5	---	
Td(on)	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3 Ω , I_D=20A	---	18.5	---	ns
T_r	Rise Time		---	9	---	
Td(off)	Turn-Off Delay Time		---	58.5	---	
T_f	Fall Time		---	32	---	
Ciss	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	3972	---	pF
Coss	Output Capacitance		---	1119	---	
Crss	Reverse Transfer Capacitance		---	82	---	
IS	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	100	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.5mH,I_{AS}=40A

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

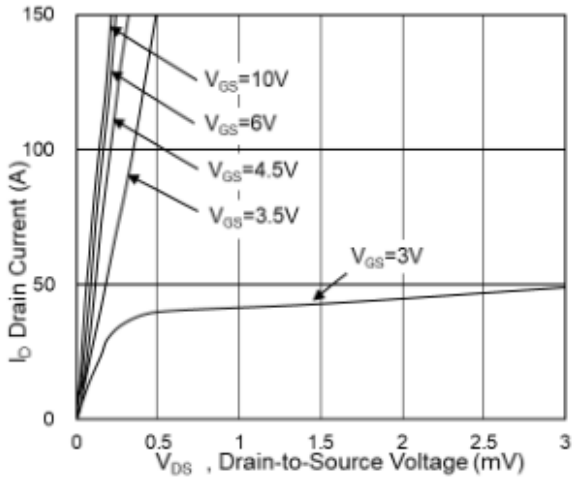


Fig.1 Typical Output Characteristics

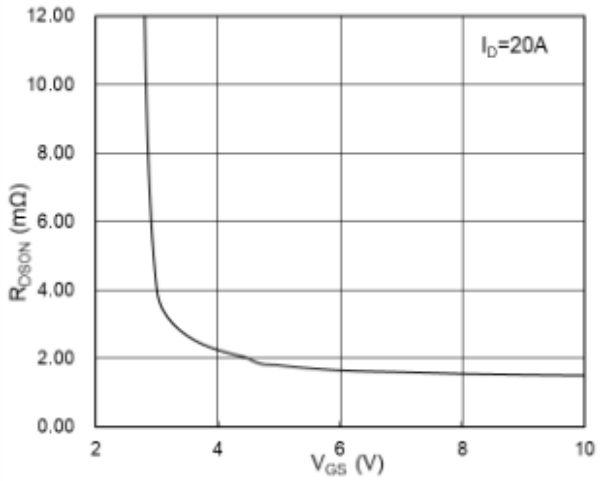


Fig.2 On-Resistance vs G-S Voltage

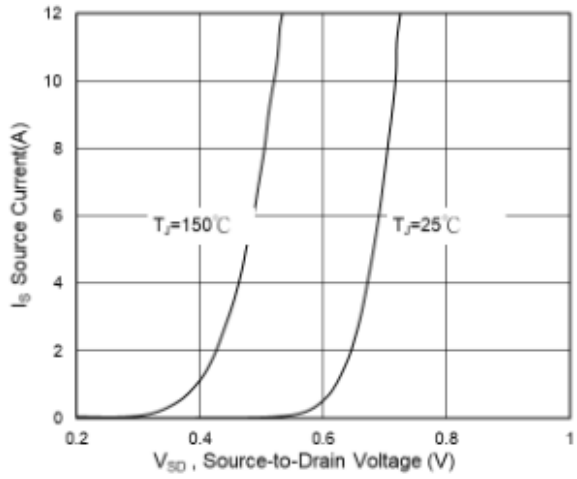


Fig.3 Source Drain Forward Characteristics

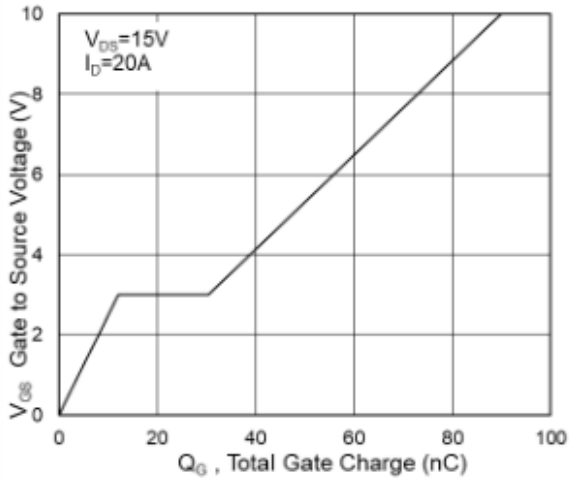


Fig.4 Gate-Charge Characteristics

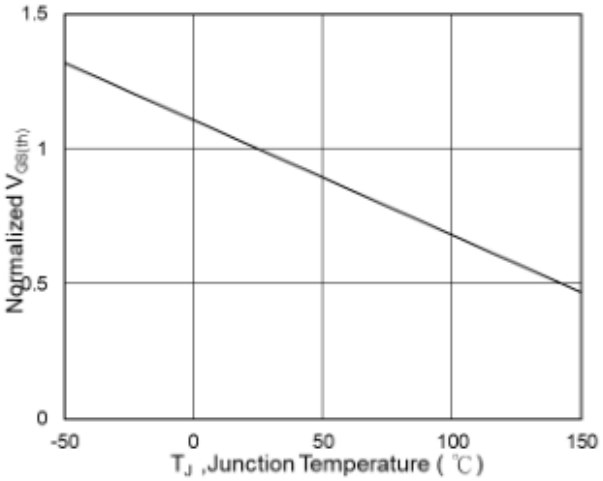


Fig.5 Normalized $V_{GS(th)}$ vs T_J

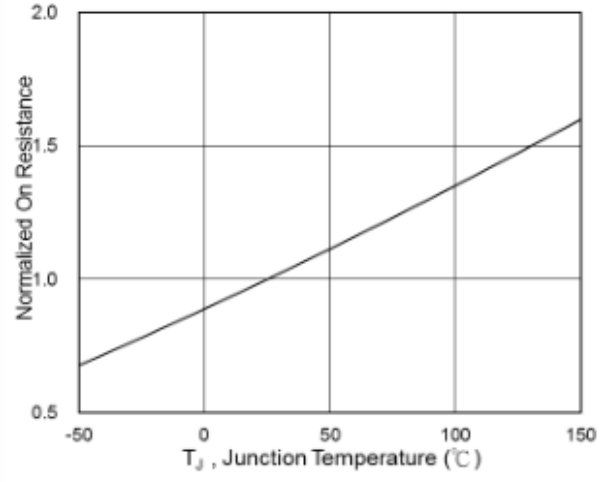


Fig.6 Normalized R_{DSON} vs T_J

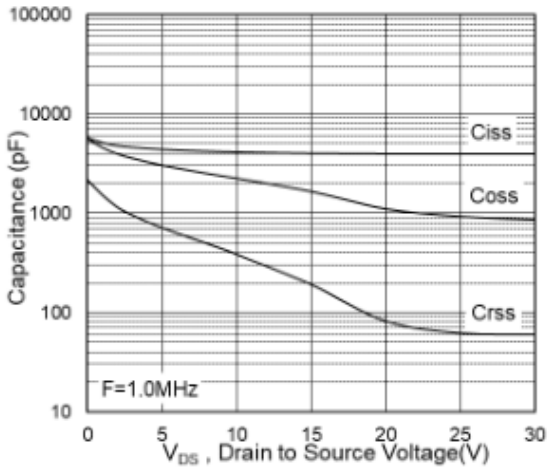


Fig.7 Capacitance

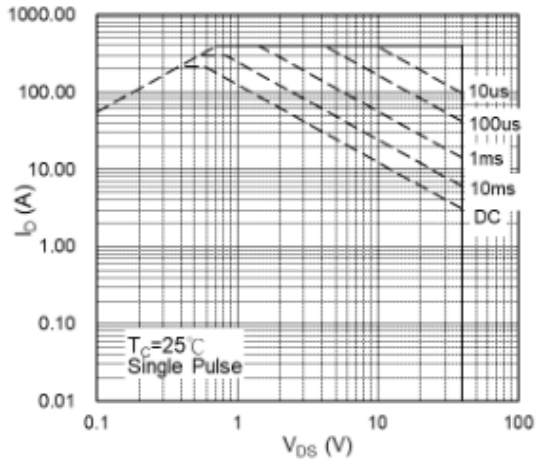


Fig.8 Safe Operating Area

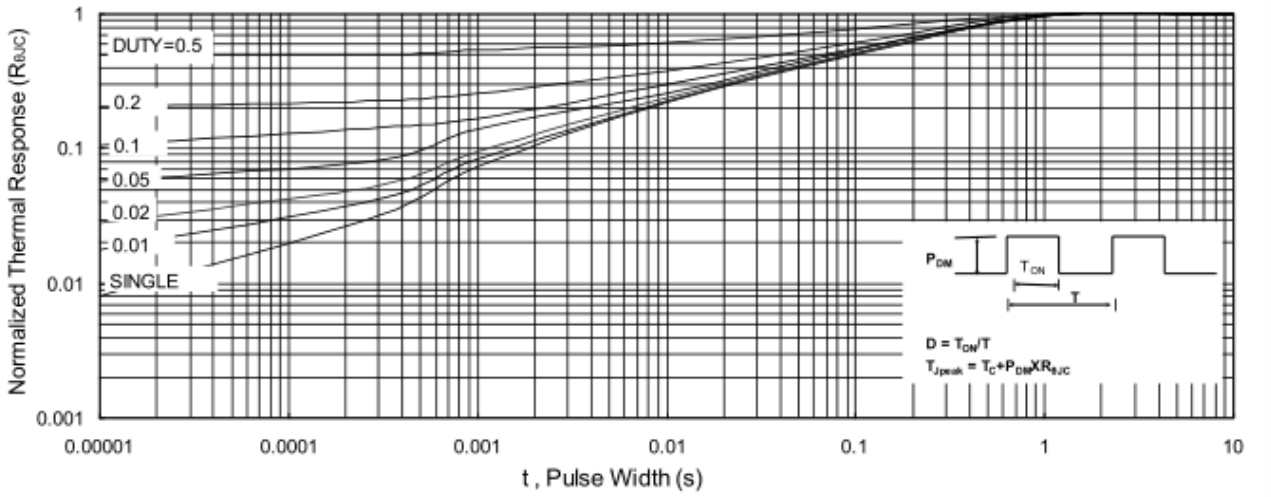


Fig.9 Normalized Maximum Transient Thermal Impedance

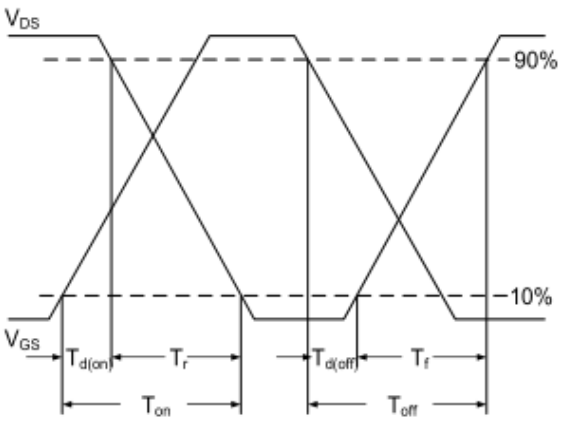


Fig.10 Switching Time Waveform

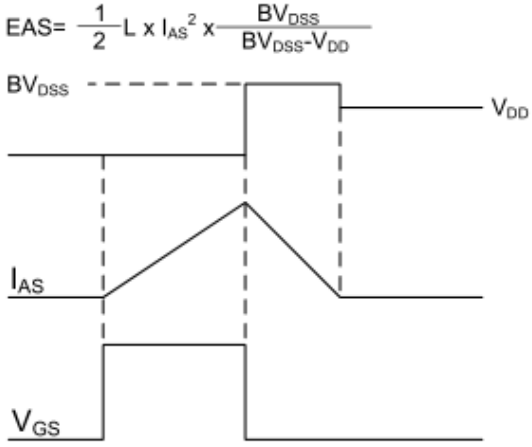
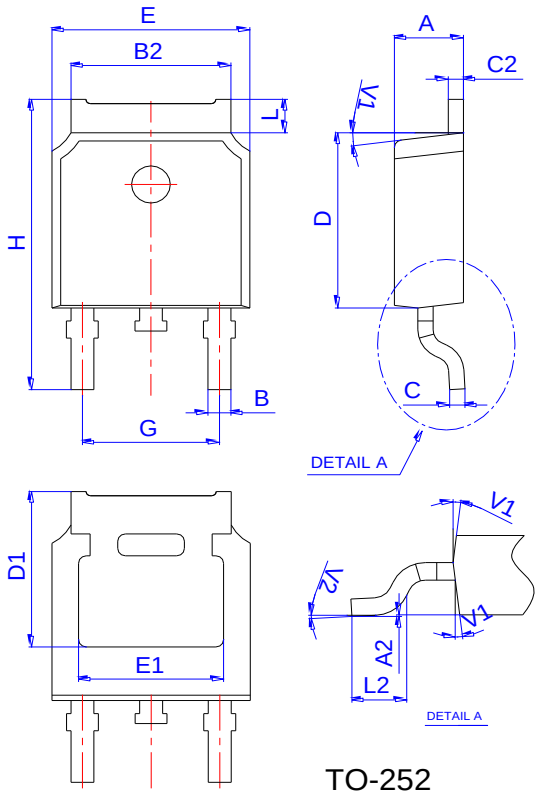


Fig.11 Unclamped Inductive Switching Waveform

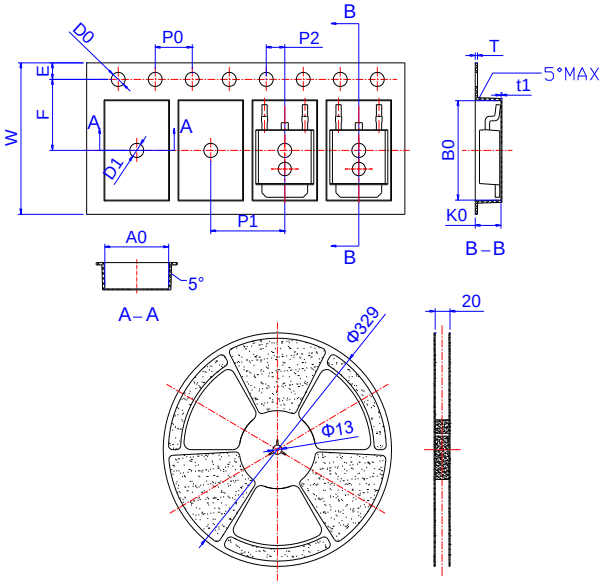
Package Mechanical Data：TO-252-3L



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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Edition	Date	Change
Rve1.0	2019/8/1	Initial release